ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	FZ1500R45KL3B5NPSA1
Manufacturer:	Infineon Technologies
Package:	Module
Availability:	Please confirm with sales

Product Page:

https://antrexco.com/product/details/infineon-technologies/fz1500r45kl3b5npsa1.html

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Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Highly insulated module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode

Features

- Electrical features
  - V_{CES} = 4500 V
  - $I_{C\ nom}$ = 1500 A / I_{CRM} = 3000 A
  - High DC stability
  - High dynamic robustness
  - Low $V_{CE,sat}$
  - Trench IGBT 3
  - $V_{CE,sat}$ with positive temperature coefficient
  - High short-circuit capability
- Mechanical features
  - High creepage and clearance distances
  - AlSiC base plate for increased thermal cycling capability
  - Package with enhanced insulation of 10.4 kV AC 60 s
  - Package with CTI > 600
  - Isolated base plate

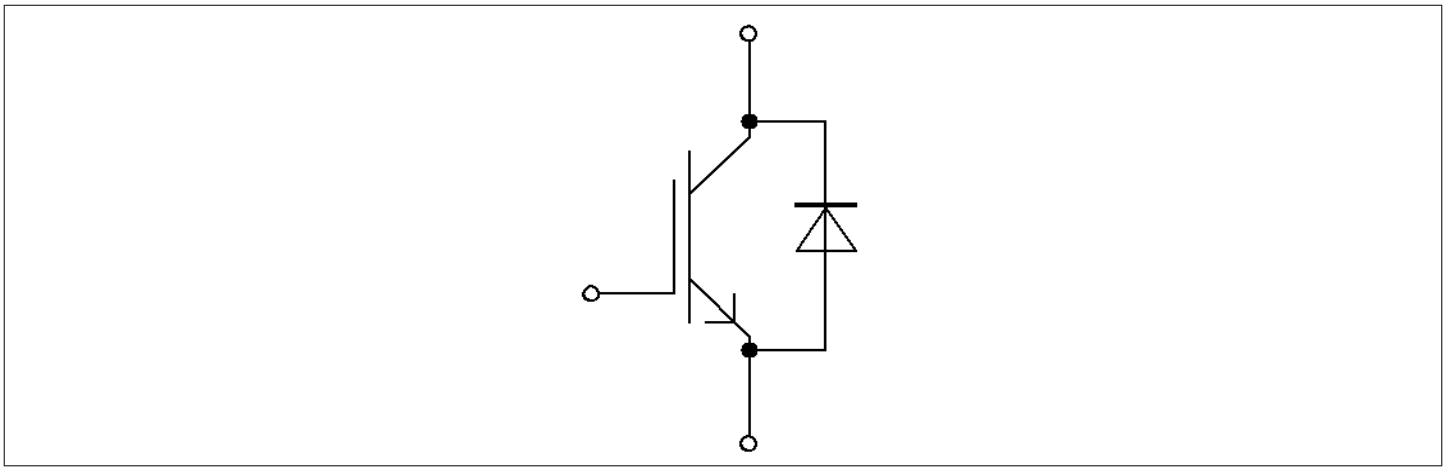
Potential applications

- High-power converters
- Medium-voltage converters
- Motor drives
- Multi-level inverter
- Traction drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 60 s	10.4	kV
Partial discharge extinction voltage	V_{isol}	RMS, f = 50 Hz, Q_{PD} ≤ 10 pC	3.5	kV
DC stability	$V_{CE(D)}$	T_{vj}=25°C, 100 Fit	3000	V
Material of module baseplate			AlSiC	
Internal isolation		basic insulation (class 1, IEC 61140)	AlN	
Creepage distance	d_{Creep}	terminal to heatsink	64.0	mm
Creepage distance	d_{Creep}	terminal to terminal	56.0	mm
Clearance	d_{Clear}	terminal to heatsink	40.0	mm
Clearance	d_{Clear}	terminal to terminal	26.0	mm
Comparative tracking index	*CTI*		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				18		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C=25°C, per switch			0.12		mΩ
Storage temperature	T_{stg}			-55		125	°C
Mounting torque for module mounting	*M*	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	*M*	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	*G*				1400		g

Note: The maximum allowed dv/dt measured between 0,6 and 1×Vce is 1400V/µs.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = -40 °C	4500	V
			T_{vj} = 25 °C	4500	
			T_{vj} = 125 °C	4500	

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 150 °C	T_C = 80 °C	1500	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		3000	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 1500 A, V_{GE} = 15 V	T_{vj} = 25 °C		2.70	3.05	V
			T_{vj} = 125 °C		3.25	3.85	
Gate threshold voltage	V_{GEth}	I_C = 105 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.40	6	6.60	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 2800 V			39.5		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0.75		Ω
Input capacitance	C_{ies}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			280		nF
Reverse transfer capacitance	C_{res}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			4.7		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 4500 V, V_{GE} = 0 V	T_{vj} = 25 °C			5	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				400	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 1500 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Gon} = 0.68 Ω	T_{vj} = 25 °C		0.910		µs
			T_{vj} = 125 °C		0.960		
Rise time (inductive load)	t_r	I_C = 1500 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Gon} = 0.68 Ω	T_{vj} = 25 °C		0.210		µs
			T_{vj} = 125 °C		0.230		
Turn-off delay time (inductive load)	t_{doff}	I_C = 1500 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Goff} = 6.2 Ω	T_{vj} = 25 °C		7.310		µs
			T_{vj} = 125 °C		7.710		
Fall time (inductive load)	t_f	I_C = 1500 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Goff} = 6.2 Ω	T_{vj} = 25 °C		1.020		µs
			T_{vj} = 125 °C		1.970		
Turn-on time (resistive load)	t_{on_R}	I_C = 500 A, V_{CC} = 2000 V, V_{GE} = ±15 V, R_{Gon} = 0.68 Ω	T_{vj} = 25 °C	1.73			µs
Turn-on energy loss per pulse	E_{on}	I_C = 1500 A, V_{CC} = 2800 V, L_σ = 110 nH, V_{GE} = ±15 V, R_{Gon} = 0.68 Ω, di/dt = 5200 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		5200		mJ
			T_{vj} = 125 °C		7500		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	I_C = 1500 A, V_{CC} = 2800 V, L_σ = 110 nH, V_{GE} = ±15 V, R_{Goff} = 6.2 Ω, dv/dt = 1300 V/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		6050		mJ
			T_{vj} = 125 °C		7750		
SC data	I_{SC}	$V_{GE} \leq$ 15 V, V_{CC} = 2800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	t_P = 10 µs, T_{vj} = 125 °C		6900		A
Thermal resistance, junction to case	R_{thJC}	per IGBT				7.40	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, λ_{grease} = 1 W/(m·K)			9.00		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-50		125	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = -40 °C	4500	V
			T_{vj} = 25 °C	4500	
			T_{vj} = 125 °C	4500	
Continuous DC forward current	I_F			1500	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		3000	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	570	kA^2s
Maximum power dissipation	P_{RQM}		T_{vj} = 125 °C	2400	kW
Minimum turn-on time	t_{onmin}			10	µs

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 1500 A, V_{GE} = 0 V	T_{vj} = 25 °C		2.80	3.40	V
			T_{vj} = 125 °C		2.70	3.20	
Peak reverse recovery current	I_{RM}	V_{CC} = 2800 V, I_F = 1500 A, V_{GE} = -15 V, -di$_F$/dt = 5200 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		1600		A
			T_{vj} = 125 °C		1800		

(table continues...)

Table 6 (continued) Characteristic values

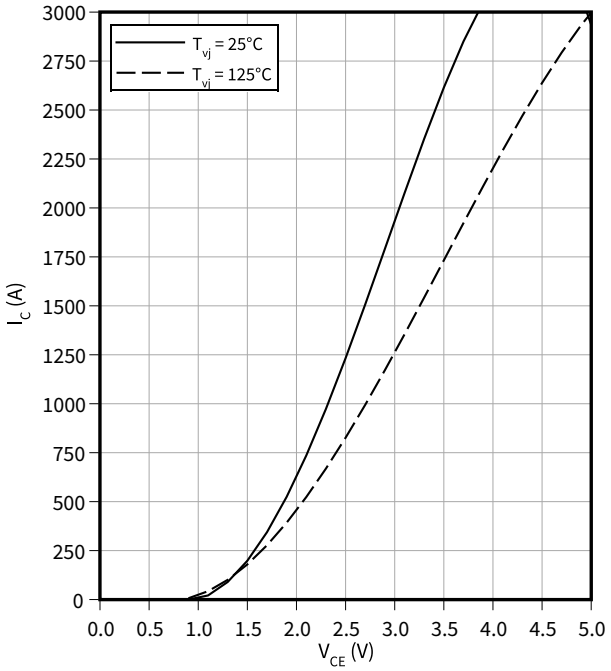
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	V_{CC} = 2800 V, I_F = 1500 A, V_{GE} = -15 V, -di$_F$/dt = 5200 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		1300		µC
			T_{vj} = 125 °C		2500		
Reverse recovery energy	E_{rec}	V_{CC} = 2800 V, I_F = 1500 A, V_{GE} = -15 V, -di$_F$/dt = 5200 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		2000		mJ
			T_{vj} = 125 °C		4300		
Thermal resistance, junction to case	R_{thJC}	per diode				17.0	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			14.0		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-50		125	°C

4 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

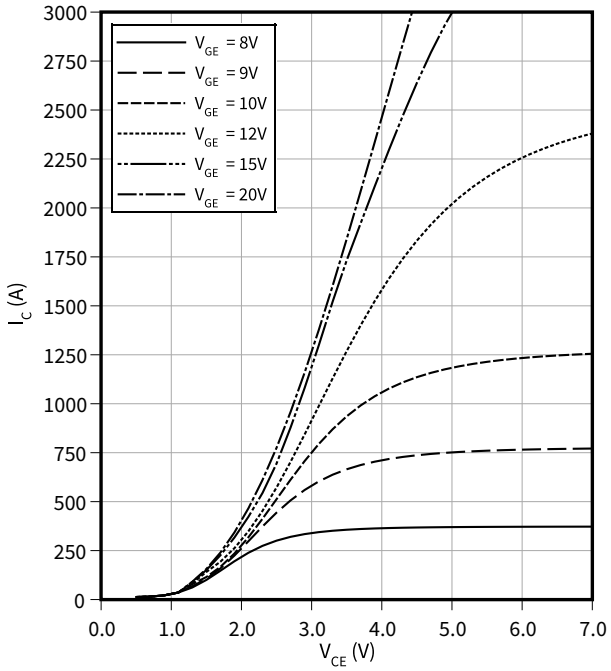
V_{GE} = 15 V



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

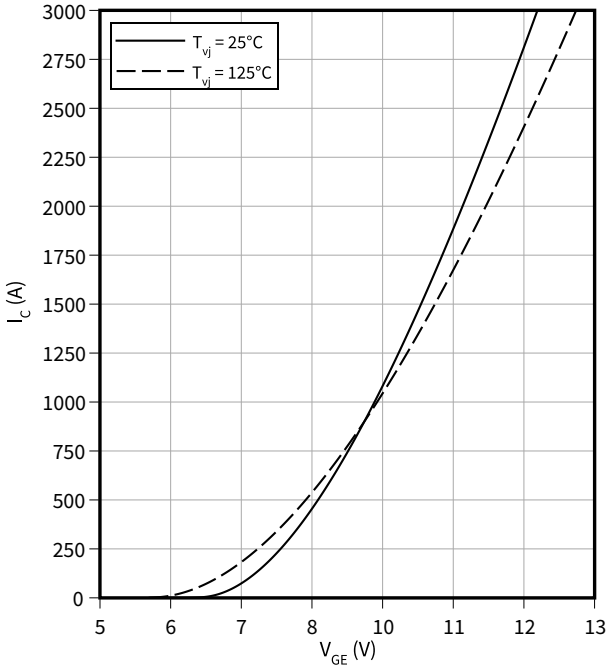
T_{vj} = 125 °C



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

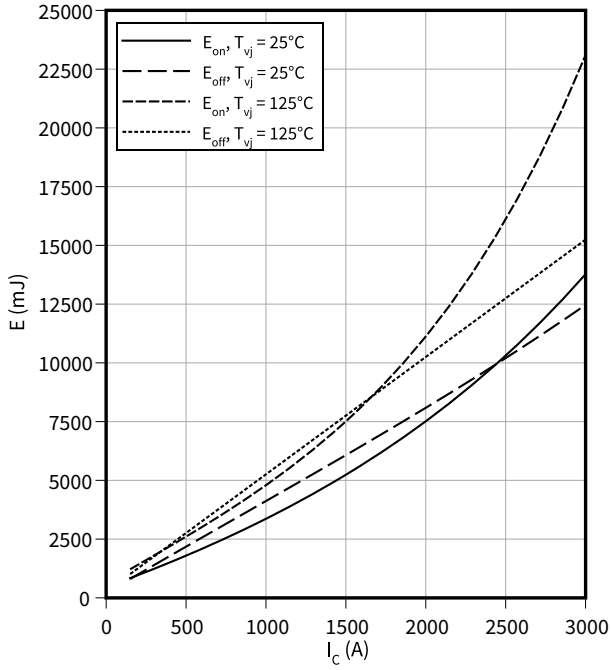
V_{CE} = 20 V



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

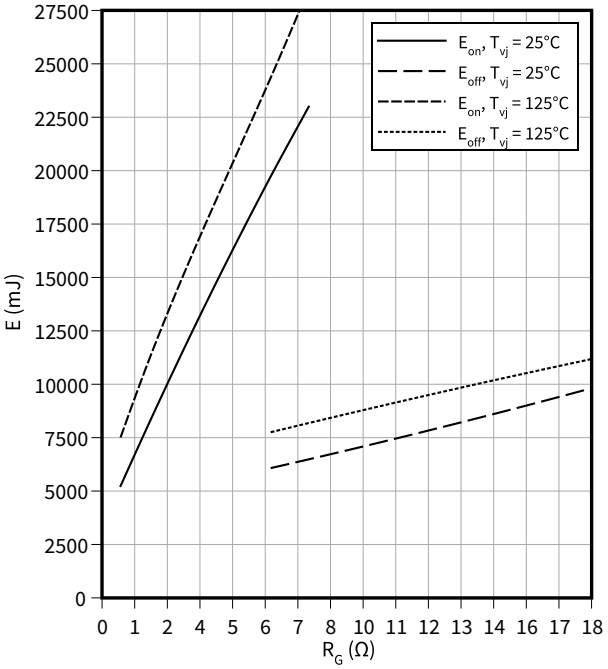
R_{Goff} = 6.2 Ω, R_{Gon} = 0.68 Ω, V_{CC} = 2800 V, V_{GE} = -15 / 15 V



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

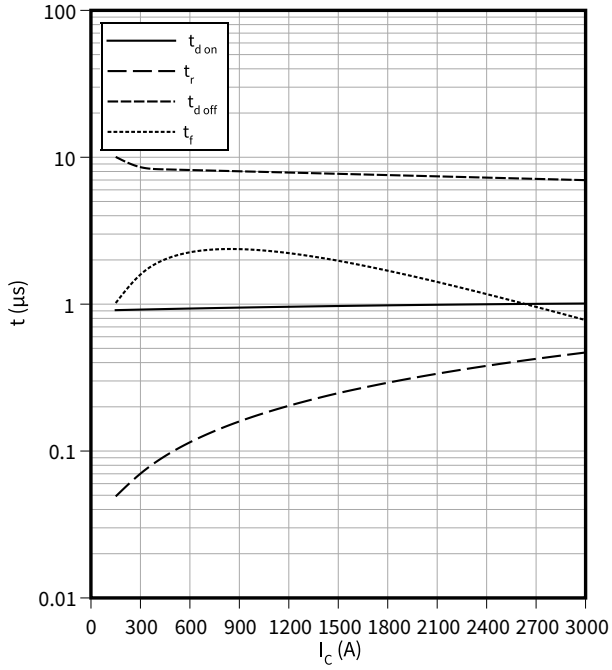
I_C = 1500 A, V_{CC} = 2800 V, V_{GE} = -15 / 15 V



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

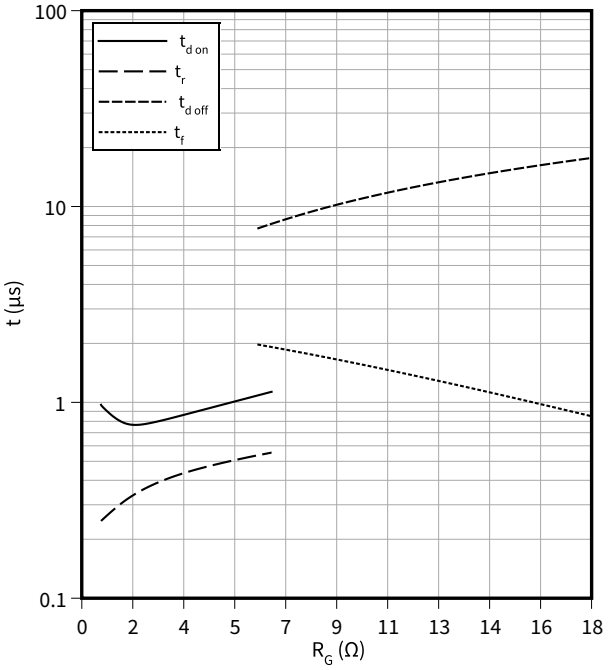
R_{Goff} = 6.2 Ω, R_{Gon} = 0.68 Ω, V_{GE} = ±15 V, V_{CC} = 2800 V, T_{vj} = 125 °C



Switching times (typical), IGBT, Inverter

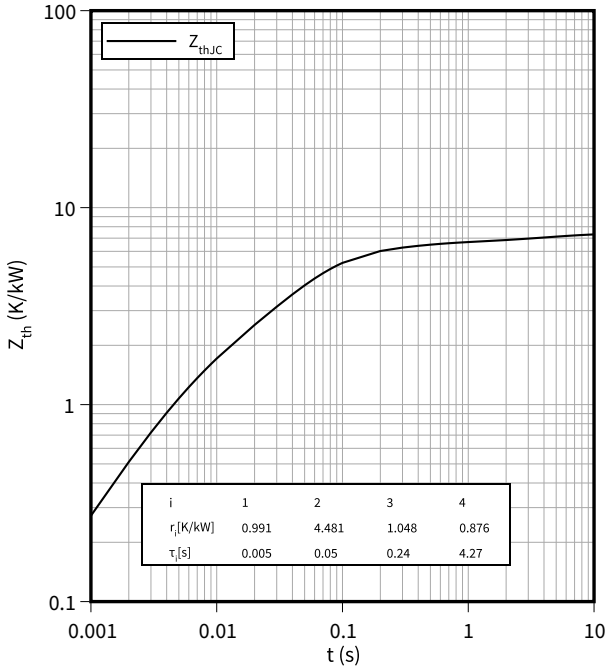
$t = f(R_G)$

V_{GE} = ±15 V, I_C = 1500 A, V_{CC} = 2800 V, T_{vj} = 125 °C



Transient thermal impedance , IGBT, Inverter

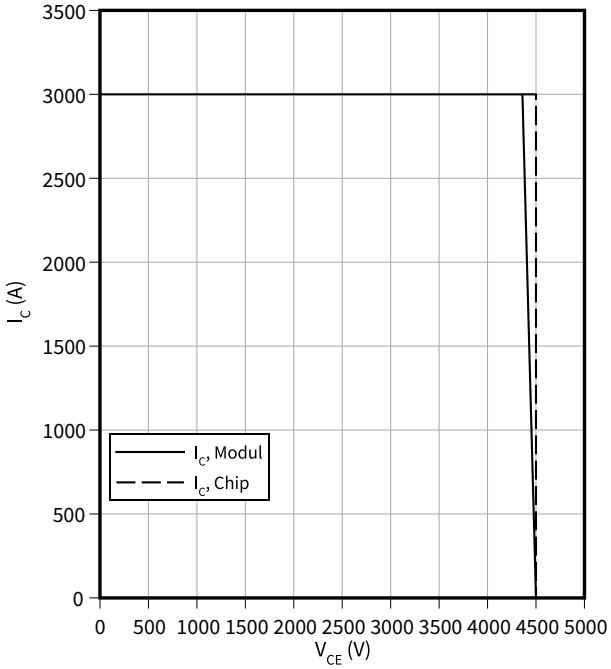
$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

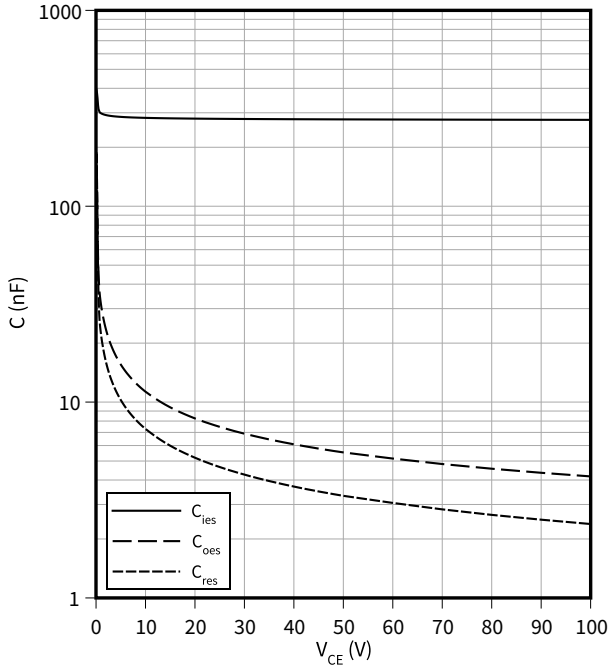
$R_{Goff} = 6.2\ \Omega$, $V_{GE} = \pm 15$ V, $T_{vj} = 125$ °C



Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

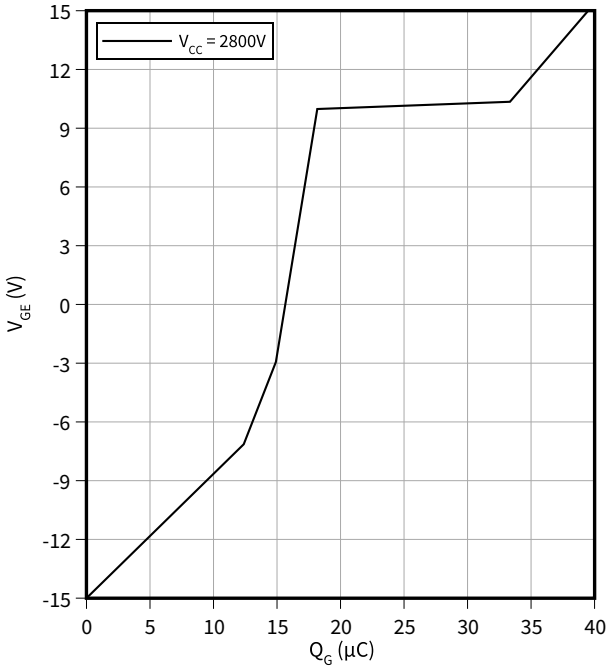
$f = 1000$ kHz, $V_{GE} = 0$ V, $T_{vj} = 25$ °C



Gate charge characteristic (typical), IGBT, Inverter

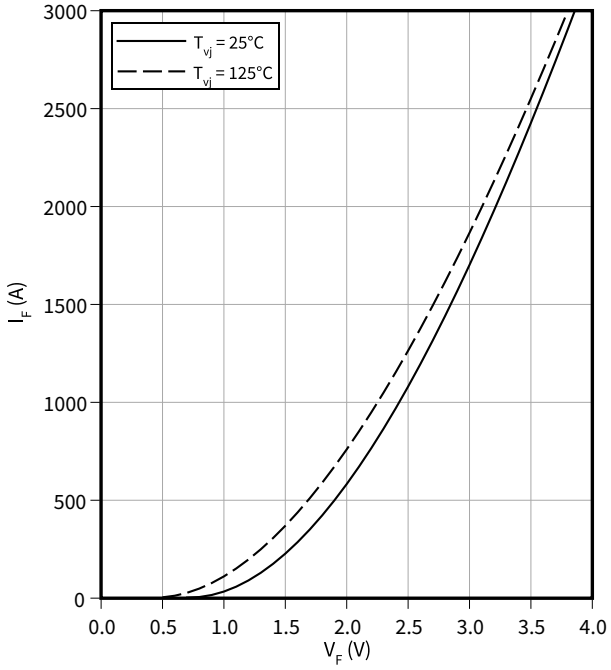
$V_{GE} = f(Q_G)$

$I_C = 1500$ A, $T_{vj} = 25$ °C



Forward characteristic (typical), Diode, Inverter

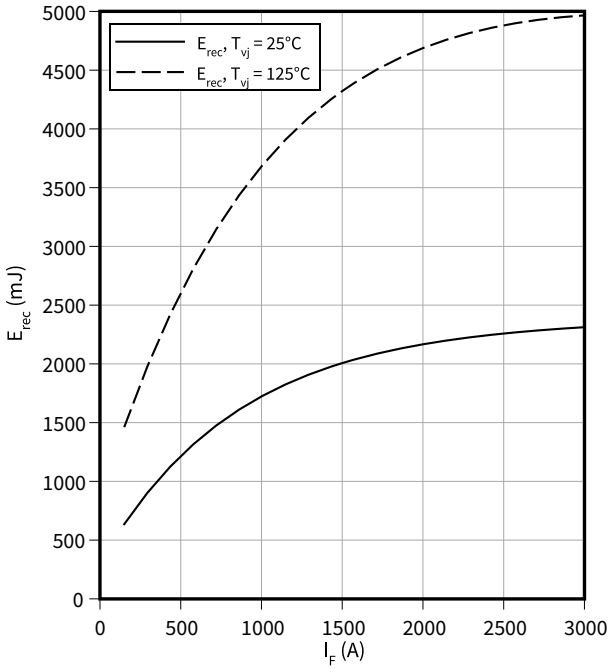
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

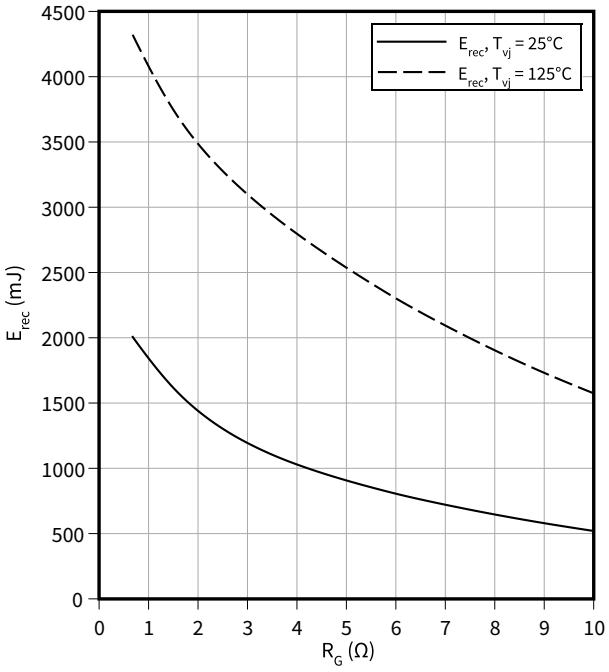
$R_{Gon} = R_{Gon}(IGBT)$, $V_{CC} = 2800$ V



Switching losses (typical), Diode, Inverter

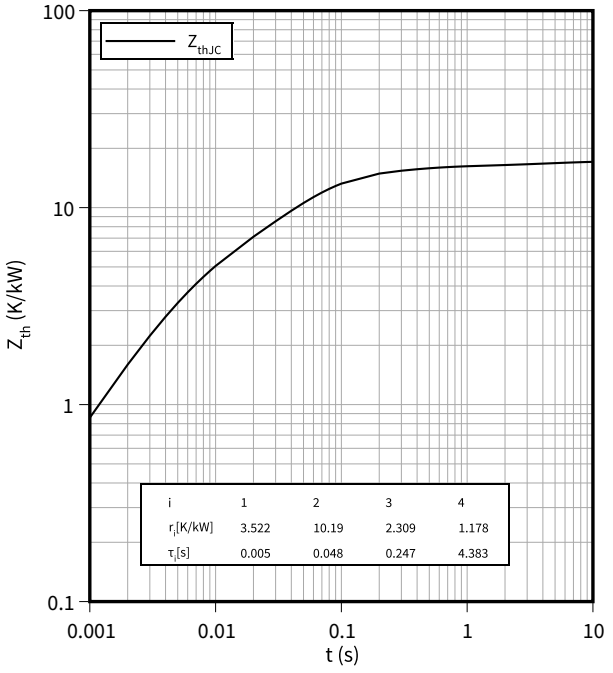
$E_{rec} = f(R_G)$

$I_F = 1500$ A, $V_{CC} = 2800$ V



Transient thermal impedance, Diode, Inverter

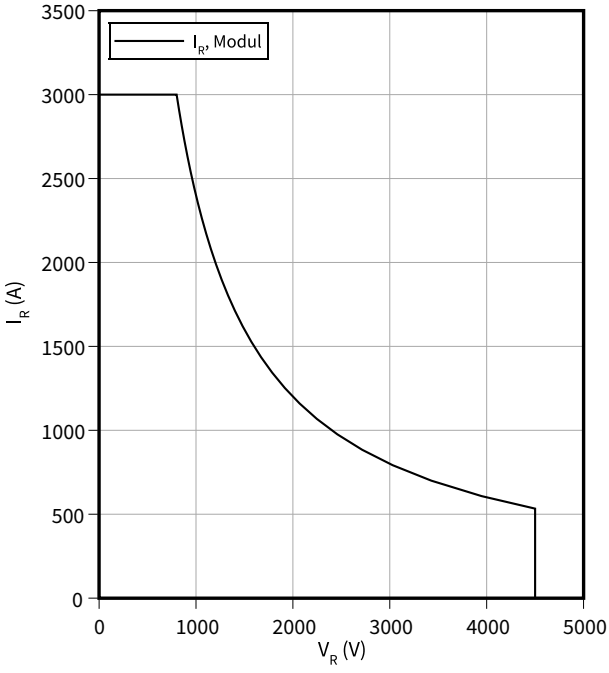
$Z_{th} = f(t)$



Safe operating area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 125$ °C



5 Circuit diagram

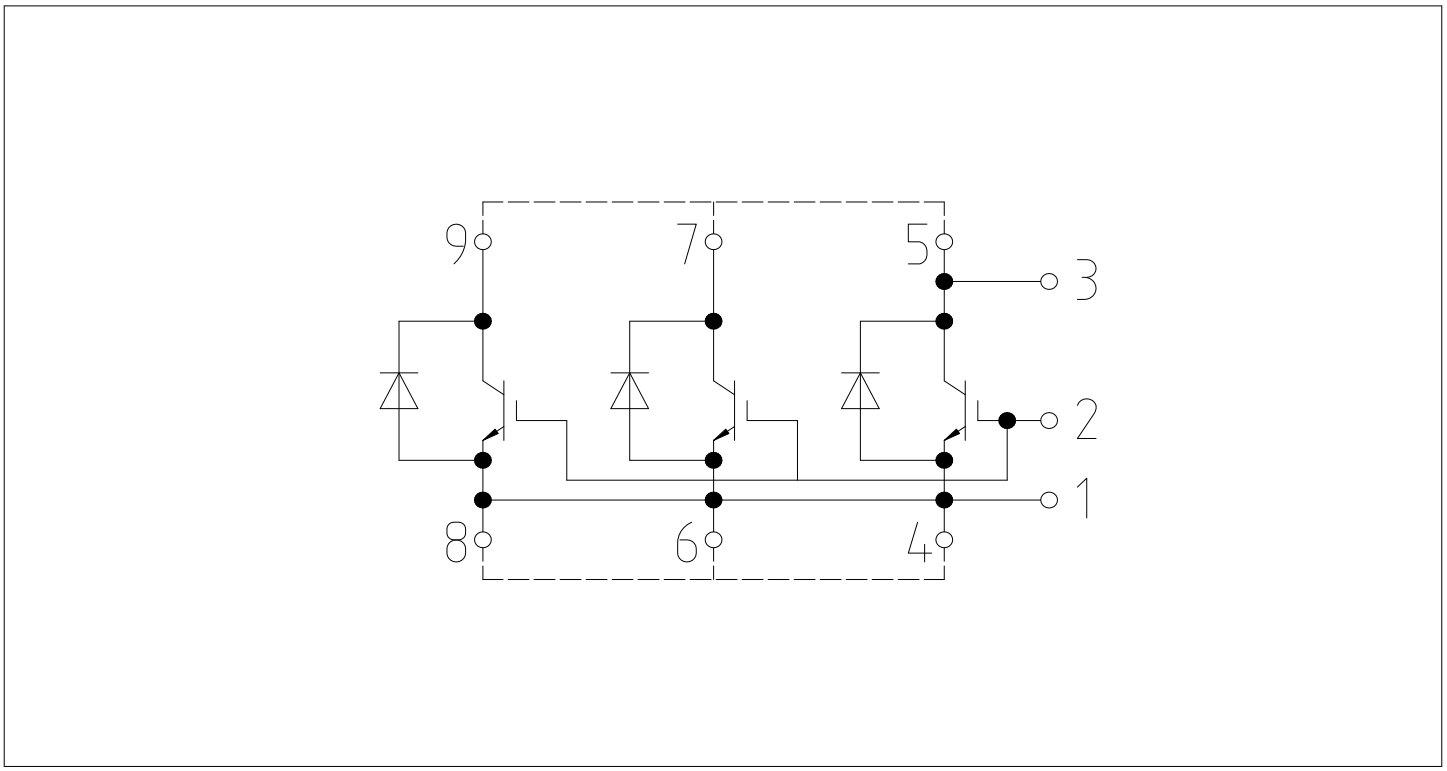


Figure 1

6 Package outlines

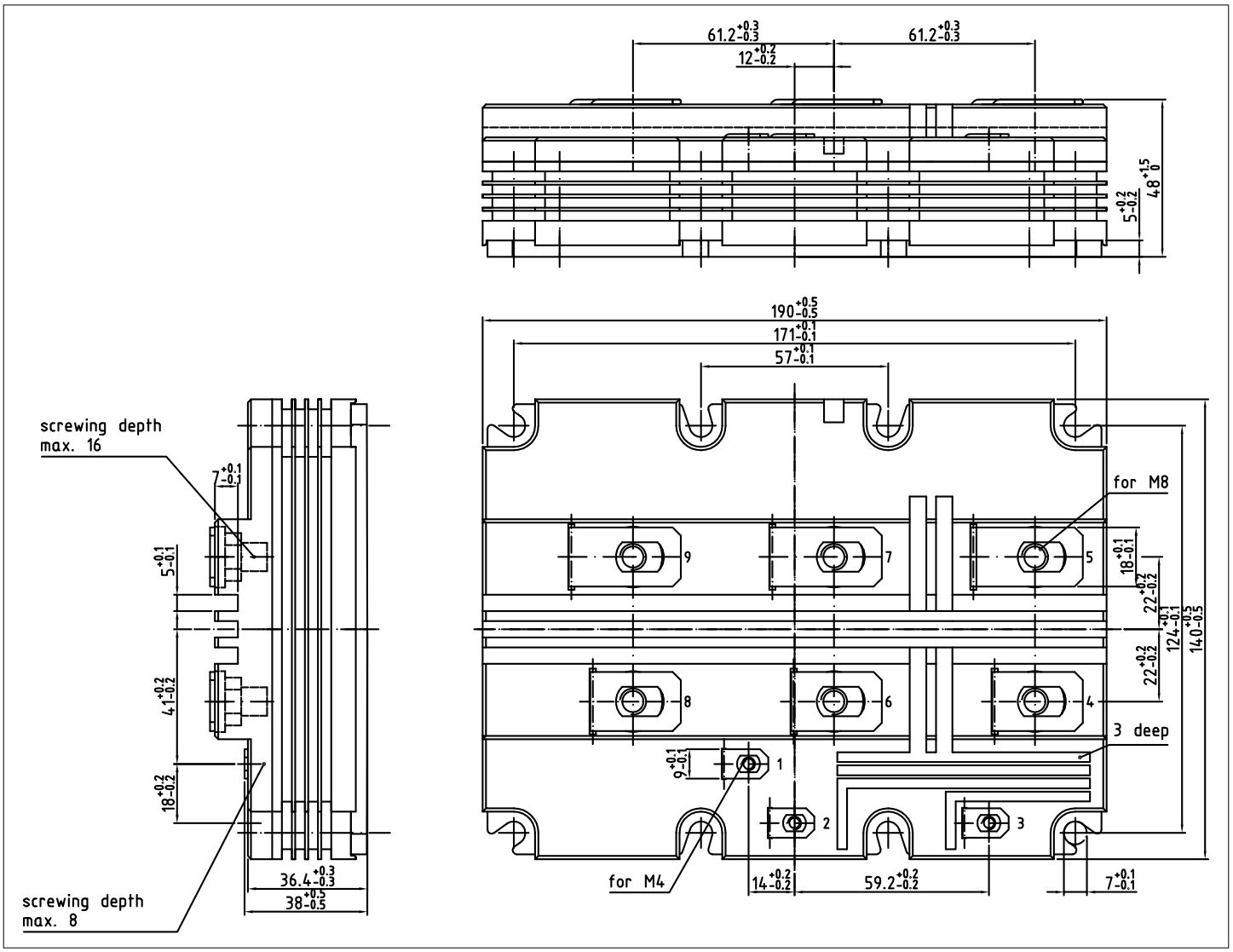


Figure 2

7 Module label code

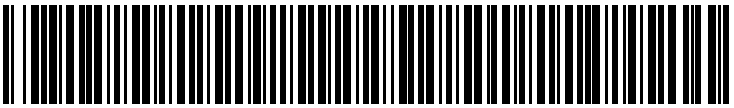
Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	 7154914284655054991530	 7154914284655054991530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-15	Initial version
0.20	2022-02-24	Target datasheet
0.30	2022-05-16	Preliminary datasheet
1.00	2022-08-15	Final datasheet

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Document reference
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